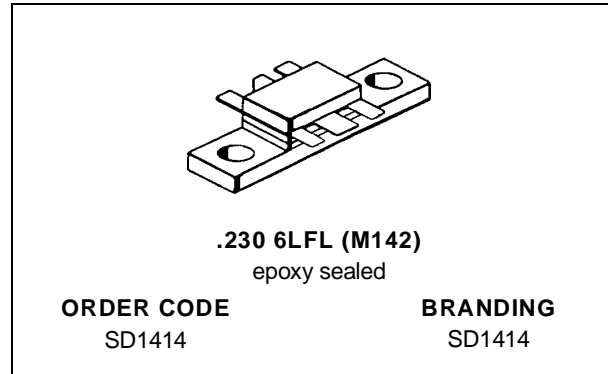
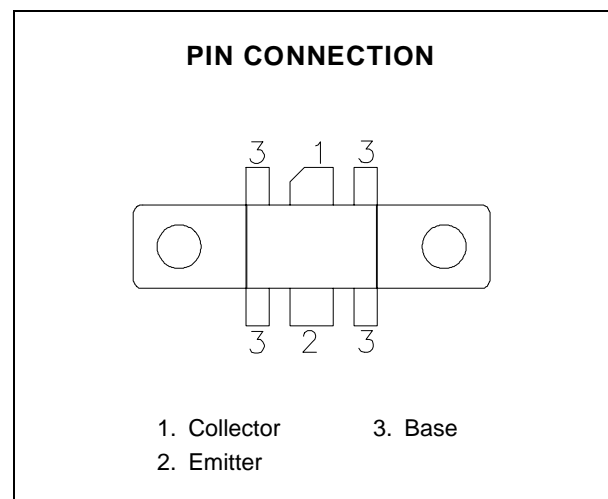


**RF & MICROWAVE TRANSISTORS
800-900 MHz APPLICATIONS**

- 836 MHz
- 12.5 VOLTS
- COMMON BASE
- P_{OUT} = 45 W MIN. WITH 4.7 dB GAIN


DESCRIPTION

The SD1414 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed for amplifier applications in the 806 - 866 MHz frequency range. Internal input matching and common base configuration assure optimum gain and efficiency across the entire frequency band. The SD1414 withstands infinite VSWR at rated power output.


ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	9.0	A
P _{DISS}	Power Dissipation	150	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	1.2	°C/W
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SD1414

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

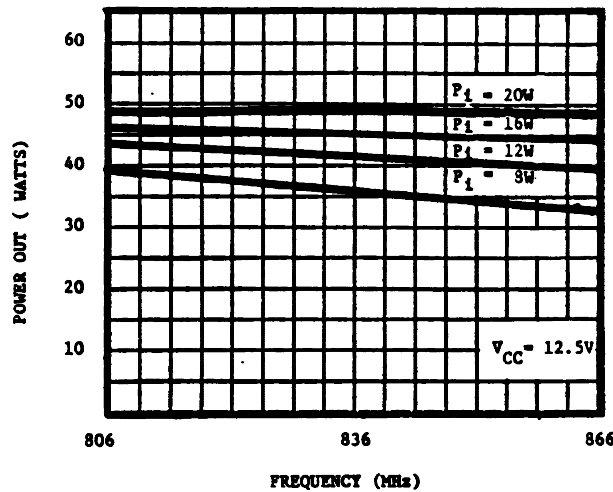
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CES}	I _C = 50mA	V _{BE} = 0V	36	—	—	V
BV _{CEO}	I _C = 50mA	I _B = 0mA	18	—	—	V
BV _{EBO}	I _E = 10mA	I _C = 0mA	4.0	—	—	V
I _{CBO}	V _{CB} = 15V	I _E = 0mA	—	—	5	mA
h _{FE}	V _{CE} = 5V	I _C = 1A	5	—	200	—

DYNAMIC

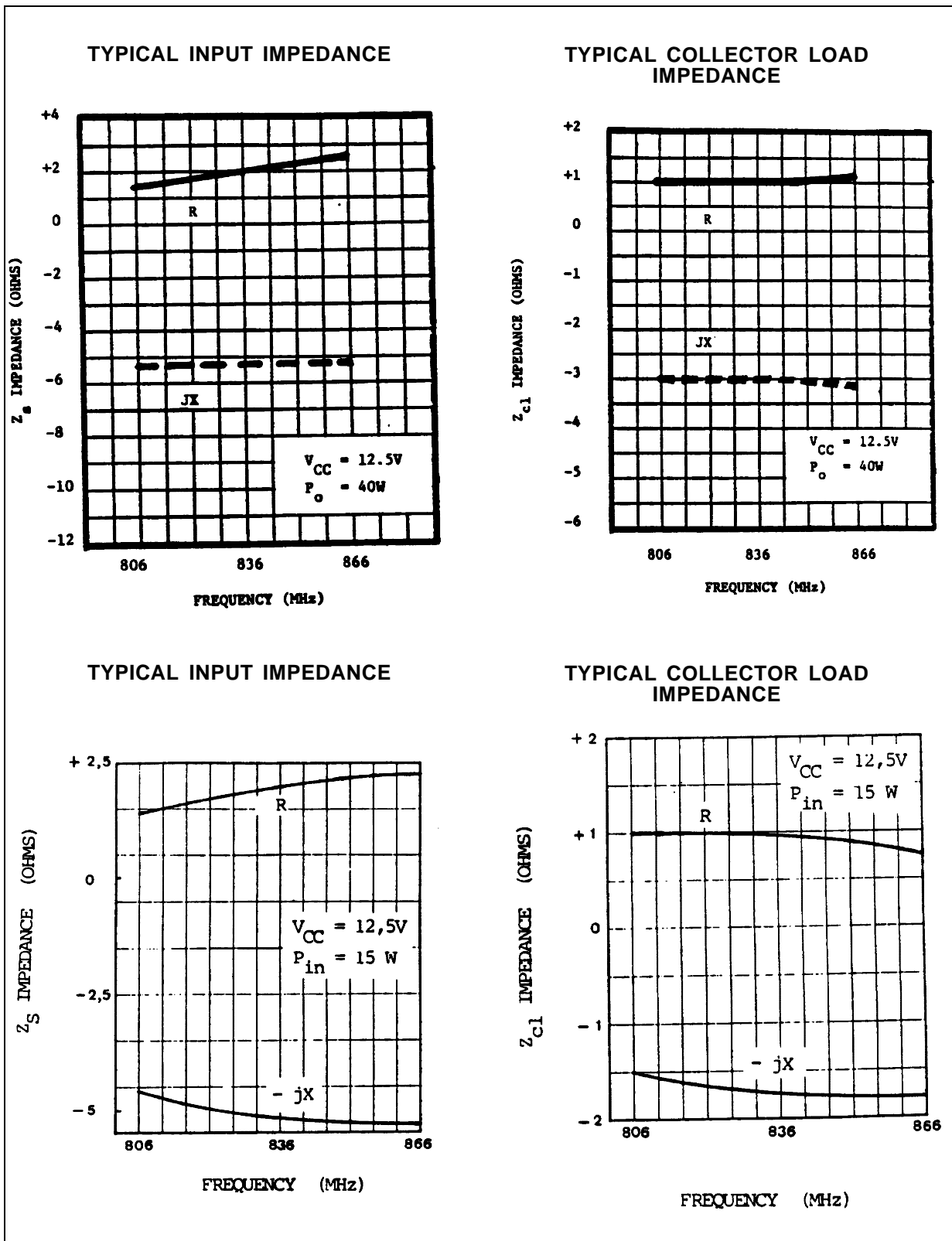
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 836 MHz	P _{IN} = 15 W	V _{CE} = 12.5 V	45	—	—	W
G _P	f = 836 MHz	P _{IN} = 15 W	V _{CE} = 12.5 V	4.7	—	—	dB
C _{OB}	f = 1 MHz	V _{CB} = 12.5 V		—	80	—	pF

TYPICAL PERFORMANCE

POWER OUTPUT vs FREQUENCY

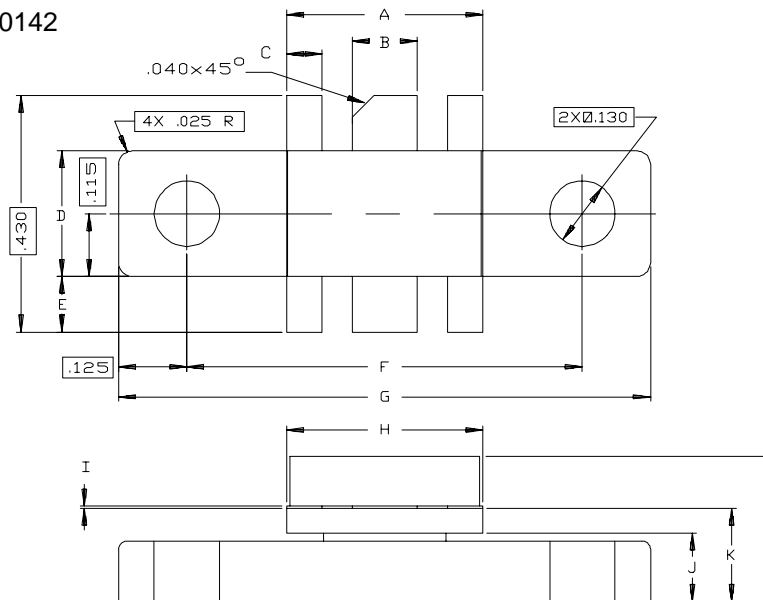


IMPEDANCE DATA



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0142



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.355/9,02	.365/9,27	K	.160/4,06	.180/4,57
B	.115/2,92	.125/3,18	L	.230/5,84	.260/6,60
C	.075/1,91	.085/2,16			
D	.225/5,72	.235/5,97			
E	.090/2,29	.110/2,79			
F	.720/18,29	.730/18,54			
G	.970/24,64	.980/24,89			
H	.355/9,02	.365/9,27			
I	.004/0,10	.006/0,15			
J	.120/3,05	.130/3,30			

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